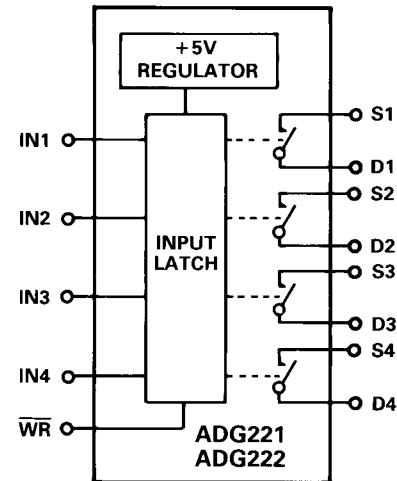


ADG221/ADG222

FEATURES

- 44V Supply Maximum Rating
- ±15V Analog Signal Range
- Low R_{ON} (60Ω)
- Low Leakage (0.5nA)
- Break-Before-Make Switching
- Extended Plastic Temperature Range
(-40°C to +85°C)
- Low Power Dissipation (25.5mW)
- μP, TTL, CMOS Compatible
- Available in 16-Lead DIP/SOIC and
20-Lead PLCC/LCCC Packages
- Surface Mount Packages
- Superior DG221 Replacement

FUNCTIONAL BLOCK DIAGRAM



GENERAL DESCRIPTION

The ADG221 and ADG222 are monolithic CMOS devices comprising four independently selectable switches. On-chip latches facilitate microprocessor interfacing. They are designed on an enhanced LC²MOS process which gives an increased signal handling capability of ±15V. These switches also feature high switching speeds and low R_{ON}.

The ADG221 and ADG222 consist of four SPST switches. They differ only in that the digital control logic is inverted. All devices exhibit break before make switching action. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

PRODUCT HIGHLIGHTS

1. Easily Interfaced:
Digital inputs are latched with a \overline{WR} signal for microprocessor interfacing. A 5V regulated supply is internally generated permitting wider tolerances on the supplies without affecting the TTL digital input switching levels.
2. Single Supply Operation:
For applications where the analog signal is unipolar (0V to 15V), the switches can be operated from a single +15V supply.
3. Low Leakage:
Leakage currents in the range of 500pA make these switches suitable for high precision circuits. The added feature of Break-before-Make switching allows for multiple outputs to be tied together for multiplexer applications while keeping leakage errors to a minimum.

| \overline{WR} | ADG221 IN | ADG222 IN | SWITCH CONDITION |
|-----------------|--------------|--------------|--------------------------------------|
| 0 | 0 | 1 | ON |
| 0 | 1 | 0 | OFF |
| 1 | X | X | Retains Previous Switch Condition |

Table 1. Truth Table

REV. B

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 Tel: 617/329-4700 Fax: 617/326-8703 Twx: 710/394-6577
 Telex: 924491 Cable: ANALOG NORWOODMASS

ADG221/ADG222—SPECIFICATIONS (V_{DD} = +15V, V_{SS} = -15V, unless otherwise specified)

| Parameter | K Version | | B Version | | T Version | | Units | Test Conditions | |
|--|-----------|----------------|-----------|----------------|-----------|-----------------|----------|--|---|
| | 25°C | -40°C to +85°C | 25°C | -40°C to +85°C | 25°C | -55°C to +125°C | | | |
| ANALOG SWITCH | | | | | | | | | |
| Analog Signal Range | ± 15 | ± 15 | ± 15 | ± 15 | ± 15 | ± 15 | Volts | - 10V ≤ V _S ≤ + 10V I _{DS} = 1.0mA Test Circuit 1 | |
| R _{ON} | 60 | | 60 | | 60 | | Ω typ | | |
| | 90 | 145 | 90 | 145 | 90 | 145 | Ω max | | |
| R _{ON} vs. V _D (V _S) | 20 | | 20 | | 20 | | % typ | V _S = 0V, I _{DS} = 1mA | |
| R _{ON} Drift | 0.5 | | 0.5 | | 0.5 | | %/°C typ | | |
| R _{ON} Match | 5 | | 5 | | 5 | | % typ | | |
| I _S (OFF) | 0.5 | | 0.5 | | 0.5 | | nA typ | V _D = ± 14V; V _S = ± 14V; Test Circuit 2 | |
| OFF Input Leakage | 2 | 100 | 2 | 100 | 1 | 100 | nA max | | |
| I _D (OFF) | 0.5 | | 0.5 | | 0.5 | | nA typ | V _D = ± 14V; V _S = ± 14V; Test Circuit 2 | |
| OFF Output Leakage | 2 | 100 | 2 | 100 | 1 | 100 | nA max | | |
| I _D (ON) | 0.5 | | 0.5 | | 0.5 | | nA typ | V _D = ± 14V; Test Circuit 3 | |
| ON Channel Leakage | 2 | 200 | 2 | 200 | 1 | 200 | nA max | | |
| DIGITAL CONTROL | | | | | | | | | |
| V _{INH} , Input High Voltage | | 2.4 | | 2.4 | | 2.4 | V min | | |
| V _{INL} , Input Low Voltage | | 0.8 | | 0.8 | | 0.8 | V max | | |
| I _{INL} or I _{INH} | | 1 | | 1 | | 1 | μA max | | |
| DYNAMIC CHARACTERISTICS | | | | | | | | | |
| t _{OPEN} | 30 | | 30 | | 30 | | ns typ | Test Circuit 4 Test Circuit 4 See Figure 2 See Figure 2 See Figure 2 V _S = 10V (p-p); f = 100kHz R _L = 75Ω; Test Circuit 6 Test Circuit 7 | |
| t _{ON} ¹ | 300 | | 300 | | 300 | | ns max | | |
| t _{OFF} ¹ | 250 | | 250 | | 250 | | ns max | | |
| t _w ¹ Write Pulse Width | | 100 | | 100 | 100 | 120 | ns min | | |
| t _S ¹ Digital Input Setup Time | | 100 | | 100 | 100 | 120 | ns min | | |
| t _H ¹ Digital Input Hold Time | | 20 | | 20 | 20 | 20 | ns min | | |
| OFF Isolation | 80 | | 80 | | 80 | | dB typ | | |
| Channel-to-Channel Crosstalk | 80 | | 80 | | 80 | | dB typ | R _S = 0Ω; C _L = 1000pF; V _S = 0V Test Circuit 5 | |
| C _S (OFF) | 5 | | 5 | | 5 | | pF typ | | |
| C _D (OFF) | 5 | | 5 | | 5 | | pF typ | | |
| C _D , C _S (ON) | 16 | | 16 | | 16 | | pF typ | | |
| C _{IN} Digital Input Capacitance | 5 | | 5 | | 5 | | pF typ | | |
| Q _{INJ} Charge Injection | 20 | | 20 | | 20 | | pC typ | | |
| POWER SUPPLY | | | | | | | | | |
| I _{DD} | 0.6 | | 0.6 | | 0.6 | | mA typ | | Digital Inputs = V _{INL} or V _{INH} |
| I _{DD} | | 1.5 | | 1.5 | | 1.5 | mA max | | |
| I _{SS} | 0.1 | | 0.1 | | 0.1 | | mA typ | | |
| I _{SS} | | 0.2 | | 0.2 | | 0.2 | mA max | | |
| Power Dissipation | | 25.5 | | 25.5 | | 25.5 | mW max | | |

NOTE

¹Sample tested at 25°C to ensure compliance.
t_{ON}, t_{OFF} are the same for both IN and WR digital input changes.
Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS*

(T_A = +25°C unless otherwise stated)

| | |
|------------------------------------|--|
| V _{DD} to V _{SS} | 44V |
| V _{DD} to GND | 25V |
| V _{SS} to GND | -25V |
| Analog Inputs ¹ | |
| Voltage at S, D | V _{SS} - 0.3V to V _{DD} + 0.3V |
| Continuous Current, S or D | 30mA |
| Pulsed Current S or D | |
| 1ms Duration, 10% Duty Cycle | 70mA |
| Digital Inputs ¹ | |
| Voltage at I _N , WR | V _{SS} - 2V to V _{DD} + 2V or 20mA, Whichever Occurs First |

Power Dissipation (Any Package)

| | |
|---|-----------------|
| Up to +75°C | 470mW |
| Derates above +75°C by | 6mW/°C |
| Operating Temperature | |
| Commercial (K Version) | -40°C to +85°C |
| Industrial (B Version) | -40°C to +85°C |
| Extended (T Version) | -55°C to +125°C |
| Storage Temperature | |
| | -65°C to +150°C |
| Lead Temperature (Soldering 10sec) | |
| | +300°C |

NOTE

¹Overvoltage at I_N, WR, S or D will be clamped by diodes. Current should be limited to the Maximum Rating above.

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one Absolute Maximum Rating may be applied at any one time.

CAUTION

ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are removed.



ORDERING GUIDE

| Model ¹ | Temperature Range | Package Option ² |
|--------------------|-------------------|-----------------------------|
| ADG221KN | -40°C to +85°C | N-16 |
| ADG221KR | -40°C to +85°C | R-16A |
| ADG221KP | -40°C to +85°C | P-20A |
| ADG221BQ | -40°C to +85°C | Q-16 |
| ADG221TQ | -55°C to +125°C | Q-16 |
| ADG221TE | -55°C to +125°C | E-20A |
| ADG222KN | -40°C to +85°C | N-16 |
| ADG222KR | -40°C to +85°C | R-16A |
| ADG222KP | -40°C to +85°C | P-20A |
| ADG222BQ | -40°C to +85°C | Q-16 |
| ADG222TQ | -55°C to +125°C | Q-16 |
| ADG222TE | -55°C to +125°C | E-20A |

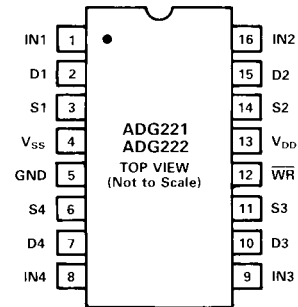
NOTES

¹To order MIL-STD-883, Class B processed parts, add /883B to T grade part numbers. See Analog Devices Military Products Databook (1990) for military data sheet.

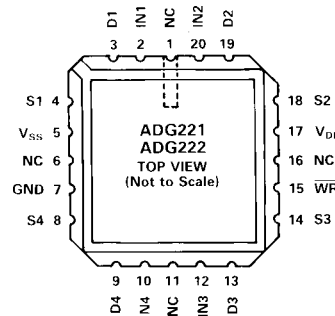
²N = Plastic DIP; R = 0.15" Small Outline IC (SOIC); P = Plastic Leaded Chip Carrier (PLCC); Q = Cerdip; E = Leadless Ceramic Chip Carrier (LCCC).

PIN CONFIGURATIONS

DIP, SOIC

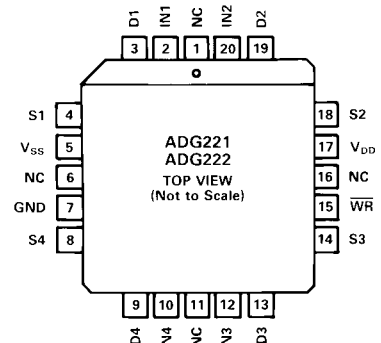


LCCC



NC = NO CONNECT

PLCC



NC = NO CONNECT

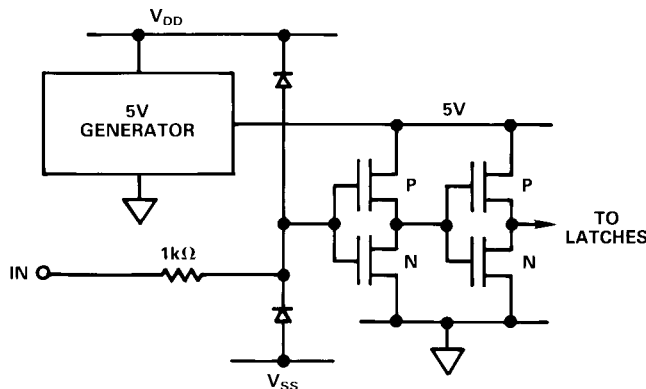
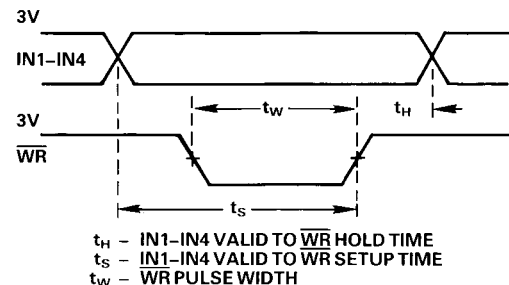


Figure 1. Typical Digital Input Cell

TIMING AND CONTROL SEQUENCE

Figure 2 shows the timing sequence for latching the switch digital inputs (IN1 – IN4). The latches are level sensitive and, therefore, while \overline{WR} is held low the latches are transparent and the switches respond to the digital inputs. The digital inputs are latched on the rising edge of \overline{WR} .

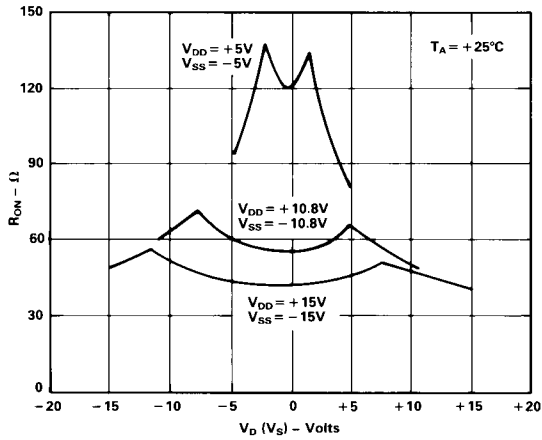


t_H – IN1-IN4 VALID TO \overline{WR} HOLD TIME
 t_S – IN1-IN4 VALID TO \overline{WR} SETUP TIME
 t_W – \overline{WR} PULSE WIDTH

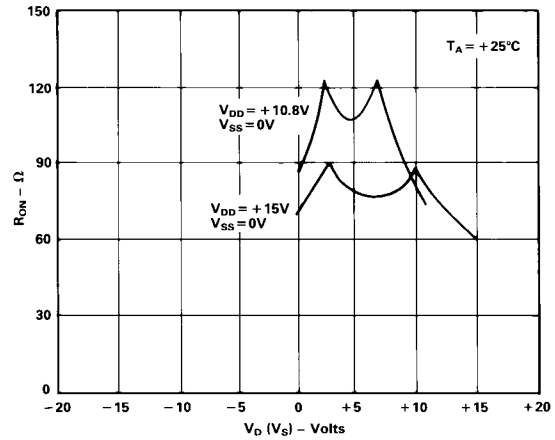
Figure 2. Timing and Control Sequence

ADG221/ADG222—Typical Performance Characteristics

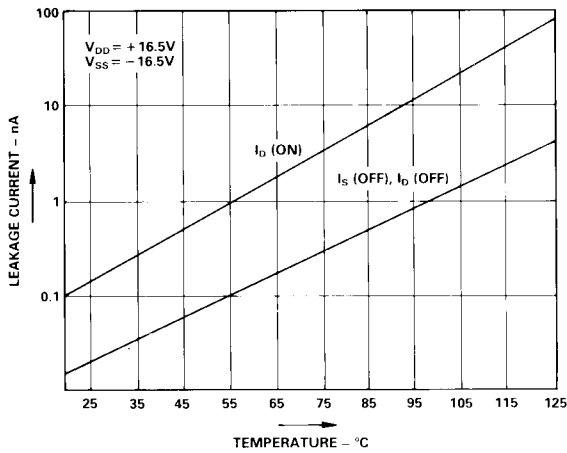
The switches are guaranteed functional with reduced single or dual supplies down to 4.5V.



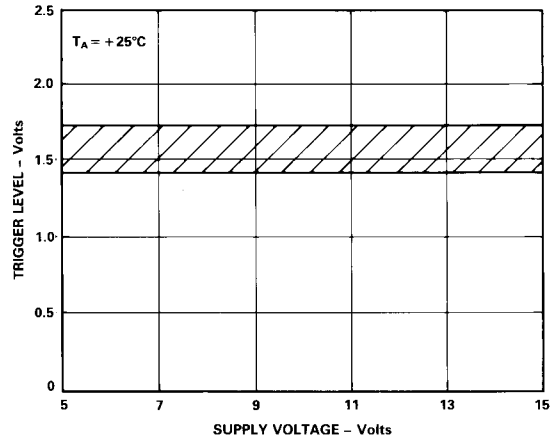
R_{ON} as a Function of V_D (V_S): Dual Supply Voltage



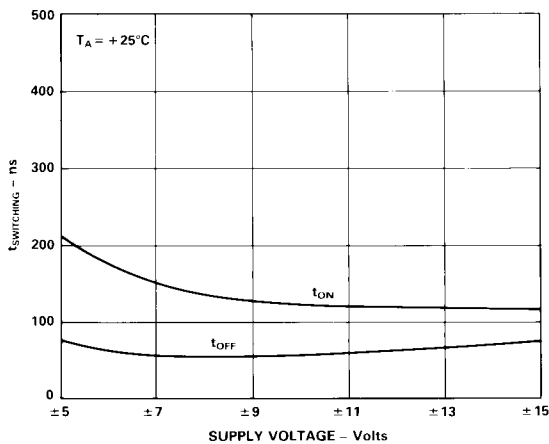
R_{ON} as a Function of V_D (V_S): Single Supply Voltage



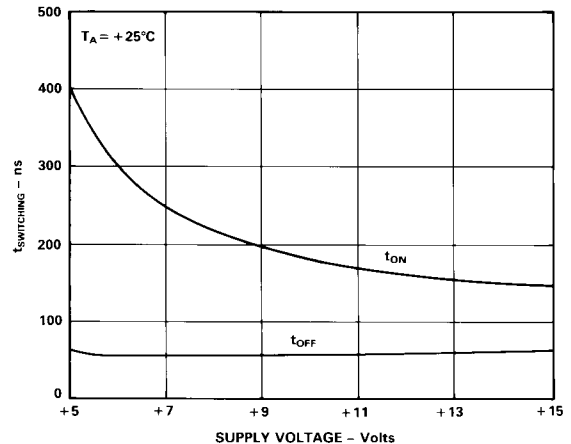
Leakage Current as a Function of Temperature (Note: Leakage Currents Reduce as the Supply Voltages Reduce)



Trigger Level vs. Power Supply Voltage: Dual or Single Supply Voltage

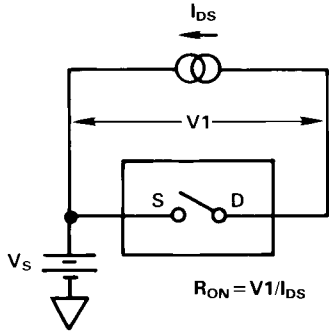


Switching Times vs. Supply Voltage (Dual Supply)

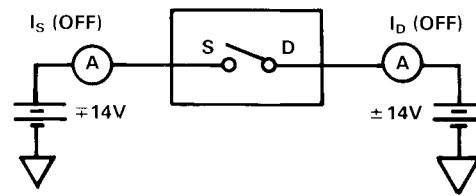


Switching Times vs. Supply Voltage (Single Supply)

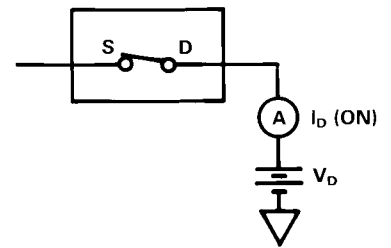
Test Circuits—ADG221/ADG222



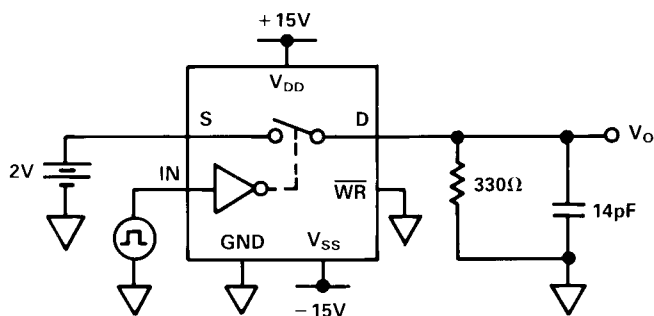
Test Circuit 1



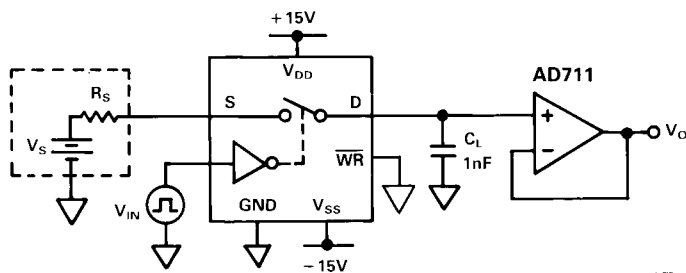
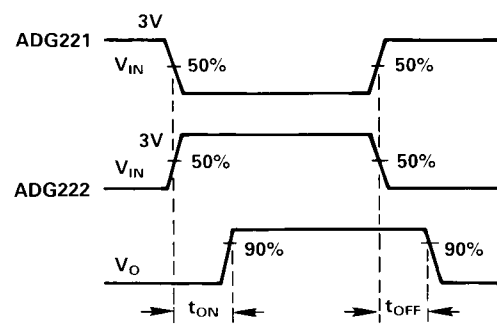
Test Circuit 2



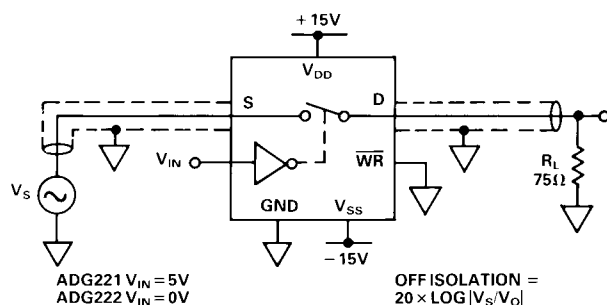
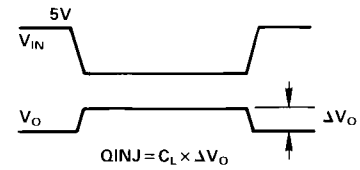
Test Circuit 3



Test Circuit 4



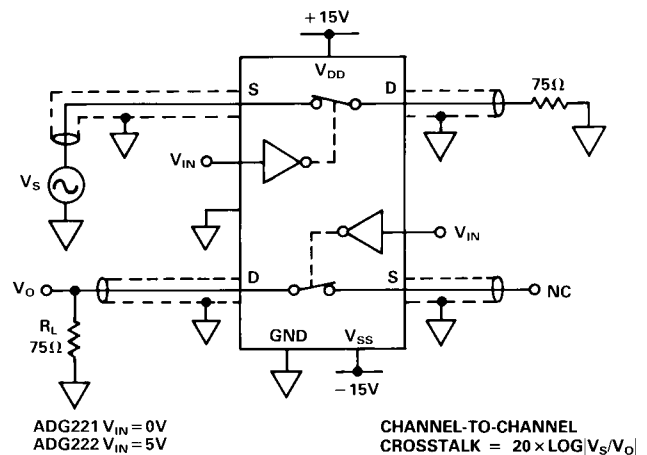
Test Circuit 5. Charge Injection



Test Circuit 6. Off Isolation

ADG221 $V_{IN} = 5V$
ADG222 $V_{IN} = 0V$

OFF ISOLATION =
 $20 \times \text{LOG} |V_S/V_O|$



Test Circuit 7. Channel-to-Channel Crosstalk

CHANNEL-TO-CHANNEL
CROSSTALK = $20 \times \text{LOG} |V_S/V_O|$

ADG221/ADG222

TERMINOLOGY

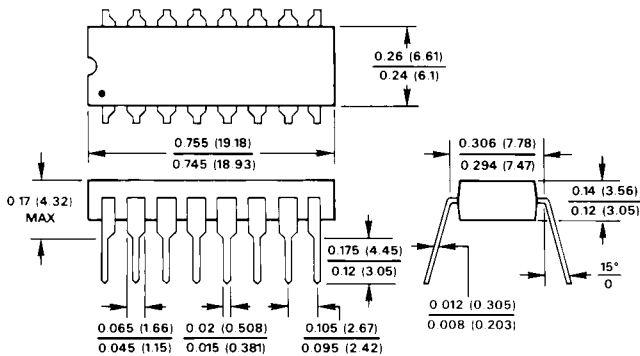
| | |
|-----------------|---|
| R_{ON} | Ohmic resistance between terminals OUT and S |
| R_{ON} Match | Difference between the R_{ON} of any two channels |
| I_S (OFF) | Source terminal leakage current when the switch is off |
| I_D (OFF) | Drain terminal leakage current when the switch is off |
| I_D (ON) | Leakage current that flows from the closed switch into the body |
| V_D (V_S) | Analog voltage on terminal D, S |
| C_S (OFF) | Switch input capacitance "OFF" condition |
| C_D (OFF) | Switch output capacitance "OFF" condition |
| C_{IN} | Digital input capacitance |
| C_D, C_S (ON) | Input or output capacitance when the switch is on |

| | |
|-------------------------|---|
| t_{ON} | Delay time between the 50% and 90% points of the digital input and switch "ON" condition |
| t_{OFF} | Delay time between the 50% and 90% points of the digital input and switch "OFF" condition |
| t_{OPEN} | "OFF" time measured between 50% points of both switches, which are connected as a multiplexer, when switching from one address state to another |
| V_{INL} | Maximum Input Voltage for a Logic Low |
| V_{INH} | Minimum Input Voltage for a Logic High |
| I_{INL} (I_{INH}) | Input current of the digital input |
| V_{DD} | Most positive voltage supply |
| V_{SS} | Most negative voltage supply |
| I_{DD} | Positive supply current |
| I_{SS} | Negative supply current |

OUTLINE DIMENSIONS

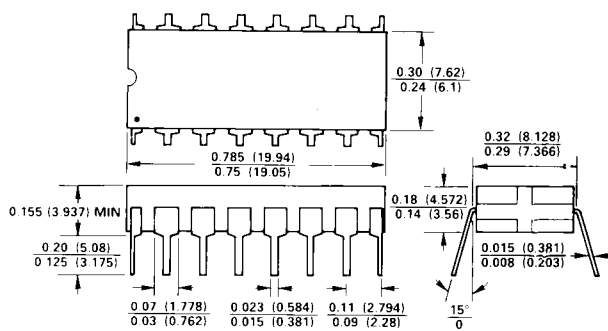
Dimensions shown in inches and (mm).

16-Pin Plastic (N-16)

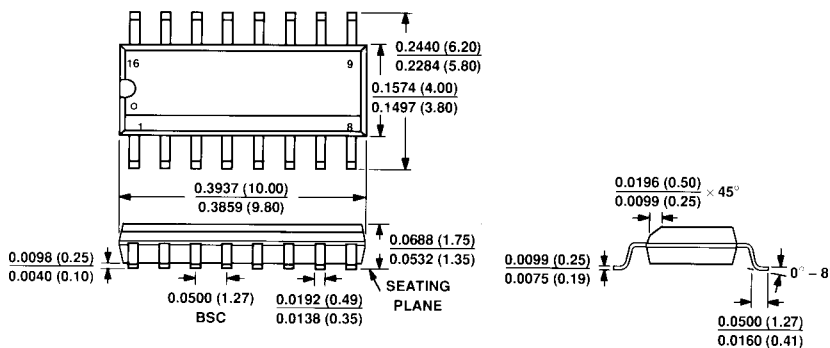


LEAD NO. 1 IDENTIFIED BY DOT OR NOTCH
LEADS ARE SOLDER OR TIN-PLATED KOVAR OR ALLOY 42

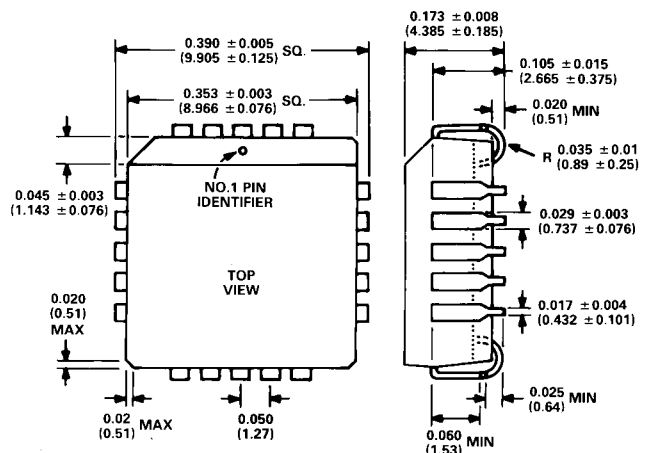
16-Pin Cerdip (Q-16)



16-Lead Narrow Body SOIC (R-16A)



20-Terminal Plastic Leaded Chip Carrier (P-20A)



20-Terminal Leadless Ceramic Chip Carrier (E-20A)

